

Abstract

A ridge waveguide type semiconductor laser of the present invention comprises, an active layer, semiconductor layers
5 formed on the active layer and having a ridge-shaped waveguide therein, an insulation film formed on the semiconductor layer, a first electrode layer in contact with the semiconductor layer through an opening provided in the insulation film, and a second
10 electrode layer formed on the first electrode layer such that it is shaped like stripes and runs in a direction of the waveguide. A distance from an end face of a resonator to an edge of the second electrode layer is within 20 μm .